

In re Patent Application of  
**GRANT**  
Serial No. Not Yet Assigned  
Filed: Herewith

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In the Claims:

Claims 1-16 (Cancelled).

17. (New) A semiconductor image sensor comprising:  
at least one pixel comprising a photosensing portion  
and a coating thereon that performs a dual function.

18. (New) A semiconductor image sensor according to  
Claim 17, wherein one of the dual functions of the coating  
comprises a fabrication function.

19. (New) A semiconductor image sensor according to  
Claim 18, wherein the fabrication function comprises the  
coating preventing silicide formation on the photosensing  
portion.

20. (New) A semiconductor image sensor according to  
Claim 17, wherein one of the dual functions of the coating  
comprises an in-use function.

21. (New) A semiconductor image sensor according to  
Claim 20, wherein the in-use function comprises the coating  
functioning as an anti-reflective surface.

22. (New) A semiconductor image sensor according to  
Claim 17, wherein the photosensing part comprises a photo-  
diode.

23. (New) A semiconductor image sensor according to  
Claim 22, wherein the photo-diode comprises a pinned photo-  
diode.

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24. (New) A semiconductor image sensor according to Claim 22, wherein the photo-diode comprises a partially pinned photo-diode.

25. (New) A semiconductor image sensor comprising:  
a substrate; and  
at least one pixel on said substrate and comprising a photosensing portion and a coating, the coating functioning as an anti-reflective surface and prevents formation of silicide on said photosensing portion.

26. (New) A semiconductor image sensor according to Claim 25, wherein the photosensing part comprises a photo-diode.

27. (New) A semiconductor image sensor according to Claim 26, wherein the photo-diode comprises a pinned photo-diode.

28. (New) A semiconductor image sensor according to Claim 26, wherein the photo-diode comprises a partially pinned photo-diode.

29. (New) A method for making a semiconductor image sensor comprising:

forming at least one pixel comprising a photosensing portion; and

forming a coating on the photosensing portion that performs a dual function.

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30. (New) A method according to Claim 29, wherein one of the dual functions of the coating comprises a fabrication function.

31. (New) A method according to Claim 30, wherein the fabrication function comprises the coating preventing silicide formation on the photosensing portion.

32. (New) A method according to Claim 29, wherein one of the dual functions of the coating comprises an in-use function.

33. (New) A method according to Claim 32, wherein the in-use function comprises the coating functioning as an anti-reflective surface.

34. (New) A method according to Claim 29, wherein forming the coating comprises a self-aligning technique.

35. (New) A method according to Claim 30, wherein the photosensing portion comprises a photo-diode.

36. (New) A method according to Claim 35, wherein the photo-diode comprises a pinned photo-diode.

37. (New) A method according to Claim 35, wherein the photo-diode comprises a partially pinned photo-diode.